

## **Description**

The ZXMP6A17K uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



## TO-252-2L

#### **General Features**

 $V_{DS} = -60V I_{D} = -10 A$ 

 $R_{DS(ON)}$  < 140m $\Omega$  @  $V_{GS}$ =10V

# G S

# **Application**

Brushless motor

Load switch

Uninterruptible power supply

P-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
ZXMP6A17K	TO-252-2L	HXY MOSFET	2500

#### Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-60	V
Vgs	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup> -10	
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup> -8.3		А
Ірм	Pulsed Drain Current <sup>2</sup>	Pulsed Drain Current <sup>2</sup> -26	
EAS	Single Pulse Avalanche Energy <sup>3</sup> 29.8		mJ
las	Avalanche Current	-24.4	А
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup> 31.3		W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup> 2		W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Reja	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	4.0	°C/W

# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

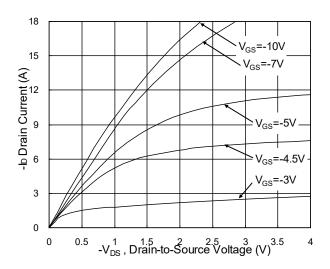
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-60			V	
$\triangle BV_{DSS}/\triangle T$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA		-0.049		V/°C	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-8A	125 140		140	0	
	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-6A		168	210	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	\/ -\/     - 2500A	-1.0		-2.5	V	
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=-250uA$		5.42		mV/°C	
1	Drain-Source Leakage Current	V <sub>DS</sub> =-48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	uA	
I <sub>DSS</sub>		V <sub>DS</sub> =-48V , V <sub>GS</sub> =0V , T <sub>J</sub> =150°C			5		
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA	
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-5A		5.8		S	
Qg	Total Gate Charge (-4.5V)			5.85		nC	
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-20V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-5A		2.9			
Q <sub>gd</sub>	Gate-Drain Charge			1.8			
T <sub>d(on)</sub>	Turn-On Delay Time			10		ns	
T <sub>r</sub>	Rise Time	$V_{DD}$ =-12V , $V_{GS}$ =-10V , $R_{G}$ =3.3 $\Omega$ ,		17			
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =-5A		22			
T <sub>f</sub>	Fall Time			21			
C <sub>iss</sub>	Input Capacitance			715			
Coss	Output Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , F=1MHz		51		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			34			
Is	Continuous Source Current <sup>1,5</sup>	V =V =0V Force Current			-9.5	Α	
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>	──V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-24	Α	
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C			-1.2	V	
t <sub>rr</sub>	Reverse Recovery Time			10.2		nS	
Q <sub>rr</sub>	Reverse Recovery Charge	IF=-8A , dl/dt=100A/μs , T <sub>J</sub> =25°C		5.4		nC	

#### Note

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2. The data tested by pulsed , pulse width  $\,\leq\,300\text{us}$  , duty cycle  $\,\leq\,2\%$
- 3. The EAS data shows Max. rating. The test condition is  $V_{DD}$ =-25V, $V_{GS}$ =-10V,L=0.1mH,I<sub>AS</sub>=-15A
- 4. The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



# **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

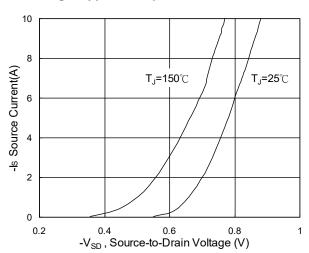


Fig.3 Forward Characteristics Of Reverse

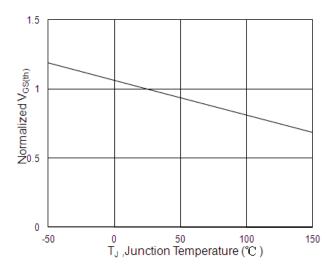


Fig.5 Normalized  $V_{\text{GS(th)}}$  vs.  $T_{\text{J}}$ 

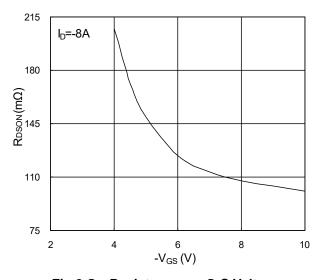


Fig.2 On-Resistance vs. G-S Voltage

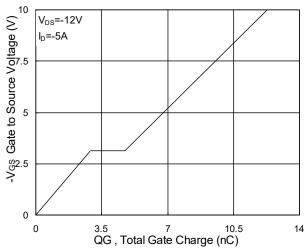


Fig.4 Gate-Charge Characteristics

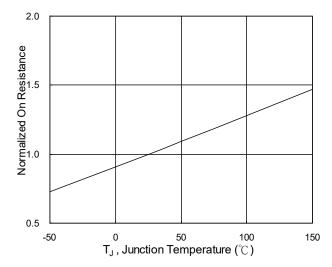
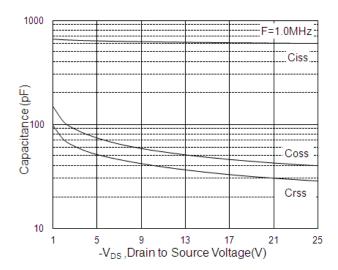


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>



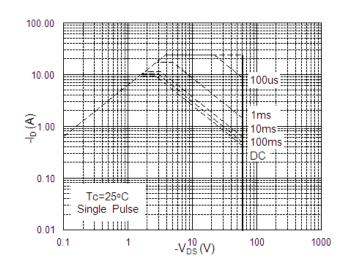


Fig.7 Capacitance

Fig.8 Safe Operating Area

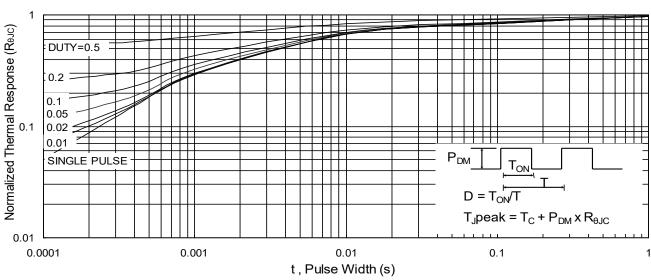


Fig.9 Normalized Maximum Transient Thermal Impedance

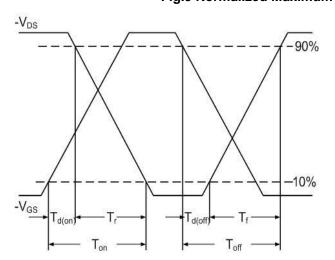


Fig.10 Switching Time Waveform

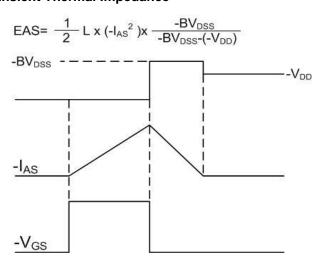
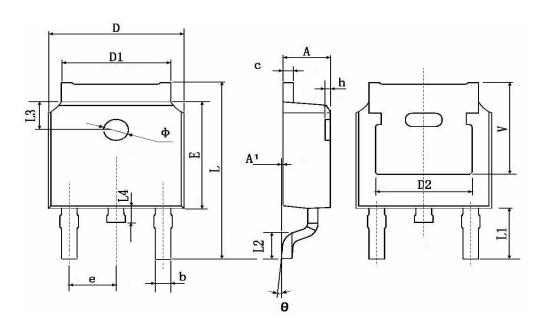


Fig.11 Unclamped Inductive Switching Waveform

# **TO-252-2L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.		0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			



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